

## 4.2 WSe<sub>2</sub> monolayer

## 5 Conclusions

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## A Approximated electron-hole interaction

In order to include excitonic effects in the real-time dynamics we derive a simplified screened exchange term. We start from the Appendix of Ref. [28]:

The KBE involves the matrix elements  $\langle m, \mathbf{k} | \Sigma^{\text{sex}} | \mathbf{m}', \mathbf{k} \rangle$ :

$$\Sigma_{m,m',\mathbf{k}}^{\text{sex}}(t) = i \sum_{\substack{\mathbf{G}, \mathbf{G}', \mathbf{q} \\ n, n'}} \rho_{m,n}(\mathbf{G}') \rho_{m',n'}^*(\mathbf{G}) W_{\mathbf{G}, \mathbf{G}'}(\mathbf{q}) \Delta\gamma_{n,n'}(t), \quad (11)$$

where  $\Delta\gamma$  is the variation of the density matrix, and  $\rho$  are the oscillators, defined as:

$$\rho_{m,n}(\mathbf{G}) = \int \varphi_{m,\mathbf{k}}^*(\mathbf{r}) \varphi_{n,\mathbf{k}-\mathbf{q}}(\mathbf{r}) e^{i(\mathbf{G}+\mathbf{q})\mathbf{r}}. \quad (12)$$

We consider only the long range part of the screened interaction  $W(\mathbf{q}) = W_{\mathbf{G}=0, \mathbf{G}'=0}(\mathbf{q})$  and the previous formula reduces to:

$$\Sigma_{m,m',\mathbf{k}}^{\text{lsex}}(t) = i \sum_{\mathbf{q}, n, n'} \rho_{m,n} \rho_{m',n'}^* W(\mathbf{q}) \Delta\gamma_{n,n'}(t). \quad (13)$$

The formula above can be rewritten in terms of time-dependent valence bands, by notice that the density matrix is expanded as:

$$\Delta\gamma_{n,m,\mathbf{k}}(t) = \sum_{l=1}^{N_v} \langle u_m | v_{l\mathbf{k}} \rangle \langle v_{l\mathbf{k}} | u_n \rangle - \delta_{n,m} f(\epsilon_{n,\mathbf{k}}) \quad (14)$$

where  $l$  is an index on valence bands while  $n, n', m, m'$  are indexes on all bands, and  $f(\epsilon_{n,\mathbf{k}})$  are the Fermi function. We can rewrite the LSEX self-energy as:

$$\Sigma_{m,m',\mathbf{k}}^{\text{lsex}} = i \sum_{\mathbf{q}, l, n, n'} \rho_{m,n} \rho_{m',n'}^* W(\mathbf{q}) \langle u_{n'} | v_{l\mathbf{k}-\mathbf{q}} \rangle \langle v_{l\mathbf{k}-\mathbf{q}} | u_n \rangle - \Sigma_{m,m',\mathbf{k}}^{\text{eq}}. \quad (15)$$

where  $\Sigma^{\text{eq}}$  is the self-energy at equilibrium, defined as:

$$\Sigma_{m,m',\mathbf{k}}^{\text{eq}} = i \sum_{\mathbf{q}, n} \rho_{m,n} \rho_{m',n}^* W(\mathbf{q}) f(\epsilon_{n,\mathbf{k}-\mathbf{q}}) \quad (16)$$

We then define the oscillators between time-dependent valence bands and Kohn-Sham states as:

$$\tilde{\rho}_{m,l} = \sum_n \rho_{m,n} \langle v_{l\mathbf{k}-\mathbf{q}} | u_n \rangle \quad (17)$$

and the previous formula reduces to:

$$\Sigma_{m,m',\mathbf{k}}^{\text{lsex}} = i \sum_{\mathbf{q},l} \tilde{\rho}_{m,l} W(\mathbf{q}) \tilde{\rho}_{m',l}^* - \Sigma_{m,m',\mathbf{k}}^{eq} \quad (18)$$

To be consistent with this approximation we excluded the local field effects in the dynamics. This approach is similar to the one used in simple models, with the difference that we calculate explicitly the matrix elements of the Coulomb interaction between the different bands at finite  $\mathbf{q}$ .

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